

LT-GaAs PCA

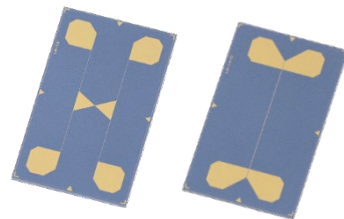
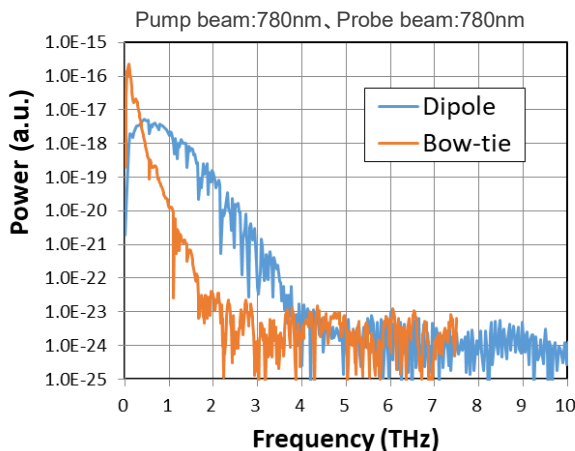
Specifications

Emitter

Bias	~20Vpp (Dipole, Bowtie)
Pump Power	~20mW@780nm ~30mW@1560nm

Detector

Carrier Lifetime	~0.5ps
Probe Power	~20mW@780nm ~30mW@1560nm



InGaAs PCA

Under development

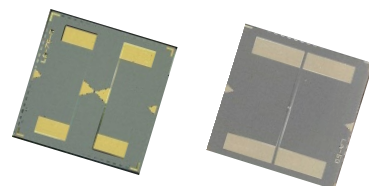
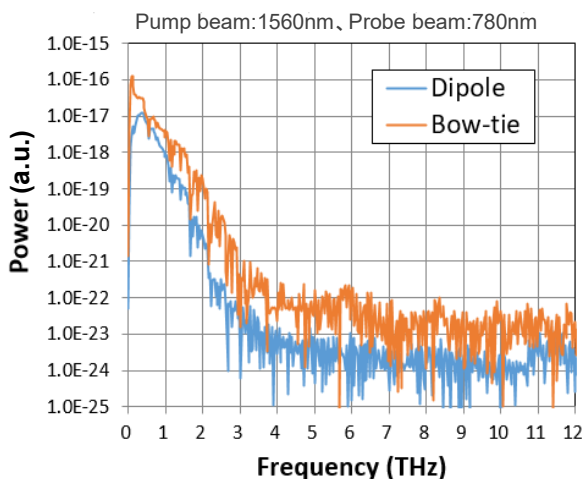
Specifications

Emitter

Bias	~40Vpp (Dipole, Bowtie)
Pump Power	~20mW@1560nm

Detector

Dynamic Range	70dB over
Frequency	5THz over
Probe Power	~20mW@1560nm



Epitaxial Wafer Grown by MBE

LT-GaAs Wafer

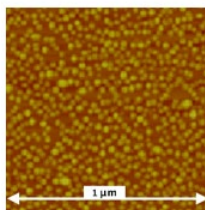
Carrier Lifetime	< 0.5ps
Resistivity	> 10 ⁵ Ωcm
Diameter	2 inch
Thickness	350μm

Quantum Dot Wafer

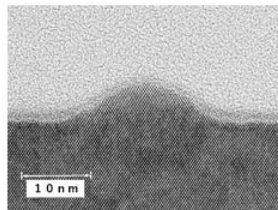
Diameter	2 inch
Material	Ga, In, Al, As, Sb, Si(n), Be(p)

InGaAs Wafer Under development

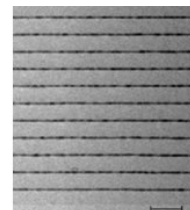
Diameter	2 inch
Thickness	350μm



Quantum Dot surface(AFM)



Quantum Dot (TEM)



Quantum Dot layer(TEM)

注意：この書類に記載の情報は予告なく変更することがある為、ご検討の際は最新の資料にてご確認ください。

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